

CBR35F-010P SERIES

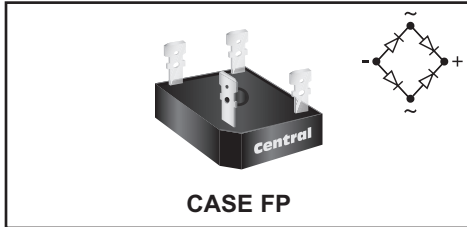
**FAST RECOVERY
SILICON BRIDGE RECTIFIERS
35 AMP, 100 THRU 600 VOLT**



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR35F-010P series devices are silicon, single phase, full wave bridge rectifiers designed for fast recovery applications. The molded epoxy case has a built-in metal baseplate for heat sink mounting. The device utilizes standard 0.25" FASTON terminals.



MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	CBR35F				UNITS
		-010P	-020P	-040P	-060P	
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	V
DC Blocking Voltage	V_R	100	200	400	600	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	V
Average Forward Current ($T_C=60^\circ\text{C}$)	I_O		35			A
Peak Forward Surge Current	I_{FSM}		400			A
RMS Isolation Voltage (case to lead)	V_{iso}		2500			Vac
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 to +150			$^\circ\text{C}$
Thermal Resistance	θ_{JC}		1.5			$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$)

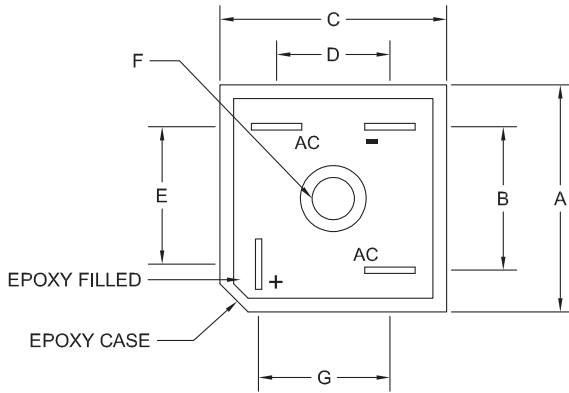
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=\text{Rated } V_{RRM}$		10	μA
V_F	$I_F=17.5\text{A}$		1.3	V
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$ (100V, 200V, 400V)		200	ns
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$ (600V)		350	ns

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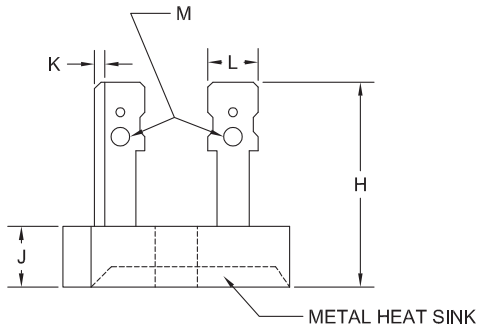
CASE FP - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.115	1.135	28.32	28.83
B	0.688	0.732	17.50	18.59
C	1.115	1.135	28.32	28.83
D	0.542	0.582	13.77	14.78
E	0.618	0.672	15.70	17.07
F (DIA.)	0.200	0.220	5.08	5.59
G	0.632	0.672	16.05	17.07
H	0.740	0.849	18.80	21.58
J	0.290	0.334	7.37	8.50
K	0.027	0.035	0.71	0.91
L	0.250		6.35	
M (DIA.)	0.940		2.39	

CASE FP (REV:R2)

MARKING: FULL PART NUMBER



R2

R1 (4-November 2013)